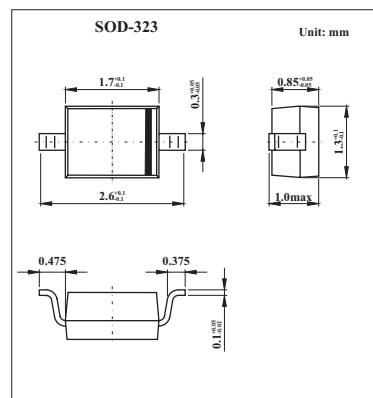


SD107WS

Features

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- Ideal for protection of MOS devices, steering, blasing, and couplong diodes for fast switching and low logic level applications.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V _R	30	Volts
Forward Current	I _F	100	mA
Forward Surge Current, tp = 10 ms	I _{FSM}	0.75	A
Power Dissipation Tc = 25 °C	P _{tot}	250(Note 1)	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	500	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _S	-65 to +150	°C

Note:

1. Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics Ta = 25°C

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage at I _R = 100 μ A	BV _R	30			Volts
Leakage Current at V _R = 25 V	I _R			1000	μ A
Forward Voltage	V _F	at I _F = 2.1 mA	260		mV
		at I _F = 15 mA	360		
		at I _F = 100 mA	470	550	
		at I _F = 200 mA	580	880	
Junction Capacitance at V _R = 10 V, f = 1.0 MHz	C _{tot}			7.0	pF

Marking

Marking	S1
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